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1      ABSTRACT OF THE DISCLOSURE

A fabrication method of a semiconductor device is disclosed. The method includes the following steps. First, a given number of projection electrodes are formed on each of a given number of semiconductor chips, and a thermosetting insulating adhesive is applied to areas of mounting parts where the semiconductor chips are to be mounted on a substrate. Second, the thermosetting insulating adhesive on the substrate is heated with a half-thermosetting temperature. Third, the semiconductor chips are aligned to the mounting parts of the substrate and a first fixing of the semiconductor chips is performed with a first pressure. Fourth, the substrate, on which the semiconductor chips are fixed, is heated with a thermosetting temperature of the thermosetting insulating adhesive, and a second fixing of the semiconductor chips is performed with a second pressure.